



## TAN150

150 Watts, 50 Volts, Pulsed  
Avionics 960 - 1215 MHz

### GENERAL DESCRIPTION

The TAN150 is a high powered COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

### ABSOLUTE MAXIMUM RATINGS

#### Maximum Power Dissipation

Device Dissipation @25°C 583 W

#### Maximum Voltage and Current

Collector to Base Voltage ( $BV_{ces}$ ) 55 V

Emitter to Base Voltage ( $BV_{ebo}$ ) 3.5 V

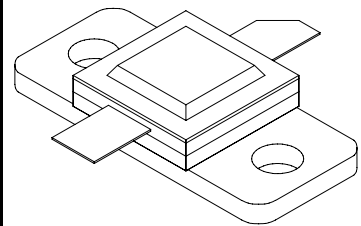
Collector Current ( $I_c$ ) 15.0 A

#### Maximum Temperatures

Storage Temperature -65 to +150 °C

Operating Junction Temperature +200 °C

### CASE OUTLINE 55AT, Style 1



### ELECTRICAL CHARACTERISTICS @ 25°C

| SYMBOL    | CHARACTERISTICS         | TEST CONDITIONS     | MIN | TYP | MAX  | UNITS |
|-----------|-------------------------|---------------------|-----|-----|------|-------|
| $P_{out}$ | Power Out               | F = 960-1215 MHz    | 150 |     |      | W     |
| $P_{in}$  | Power Input             | $V_{cc} = 50$ Volts |     |     | 30   | W     |
| $P_g$     | Power Gain              | PW = 20 $\mu$ sec   | 7.0 |     |      | dB    |
| $\eta_c$  | Collector Efficiency    | DF = 5%             |     | 38  |      | %     |
| VSWR      | Load Mismatch Tolerance | F = 1090 MHz        |     |     | 10:1 |       |

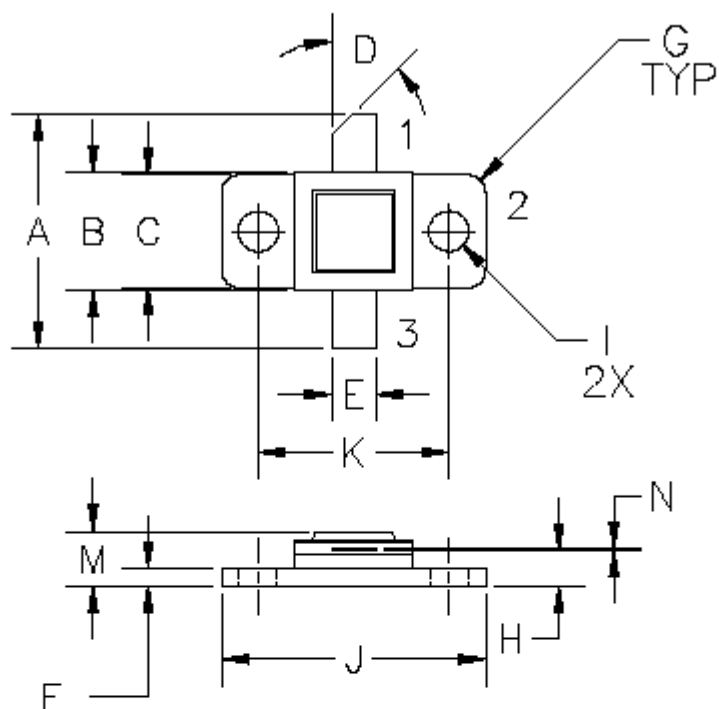
### FUNCTIONAL CHARACTERISTICS @ 25°C

|                 |                                |                          |     |  |     |      |
|-----------------|--------------------------------|--------------------------|-----|--|-----|------|
| $BV_{ebo}$      | Emitter to Base Breakdown      | $I_e = 10$ mA            | 3.5 |  |     | V    |
| $BV_{ces}$      | Collector to Emitter Breakdown | $I_c = 50$ mA            | 55  |  |     | V    |
| $h_{FE}$        | DC – Current Gain              | $V_{ce} = 5V, I_c = 1$ A | 10  |  |     |      |
| $\theta_{jc}^1$ | Thermal Resistance             |                          |     |  | 0.3 | °C/W |

NOTE 1: At rated output power and pulse conditions

Rev A: Updated June 2009

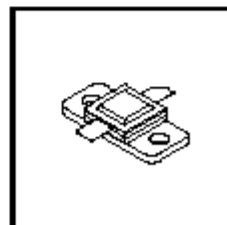
# TAN150 CASE DRAWING:



| DIM | MILLIMETER | ±TOL | INCHES   | ±TOL |
|-----|------------|------|----------|------|
| A   | 20.32      | .76  | .800     | .050 |
| B   | 10.16      | .13  | .400     | .005 |
| C   | 9.78       | .13  | .385     | .005 |
| D   | 45°        | 5°   | 45°      | 5°   |
| E   | 3.81       | .13  | .150     | .005 |
| F   | 1.47       | .25  | .058     | .010 |
| G   | 1.52R      | .13  | .060R    | .005 |
| H   | 3.05       | .25  | .120     | .010 |
| I   | 3.25 DIA   | .13  | .128 DIA | .005 |
| J   | 22.86      | .13  | .900     | .005 |
| K   | 16.51      | .13  | .650     | .005 |
| M   | 4.70       | REF  | .185     | REF  |
| N   | 0.10       | .02  | .004     | .001 |

**STYLE 1:**  
**PIN 1 = COLLECTOR**  
**2 = BASE**  
**3 = EMITTER**

**STYLE 2:**  
**PIN 1 = COLLECTOR**  
**2 = EMITTER**  
**3 = BASE**



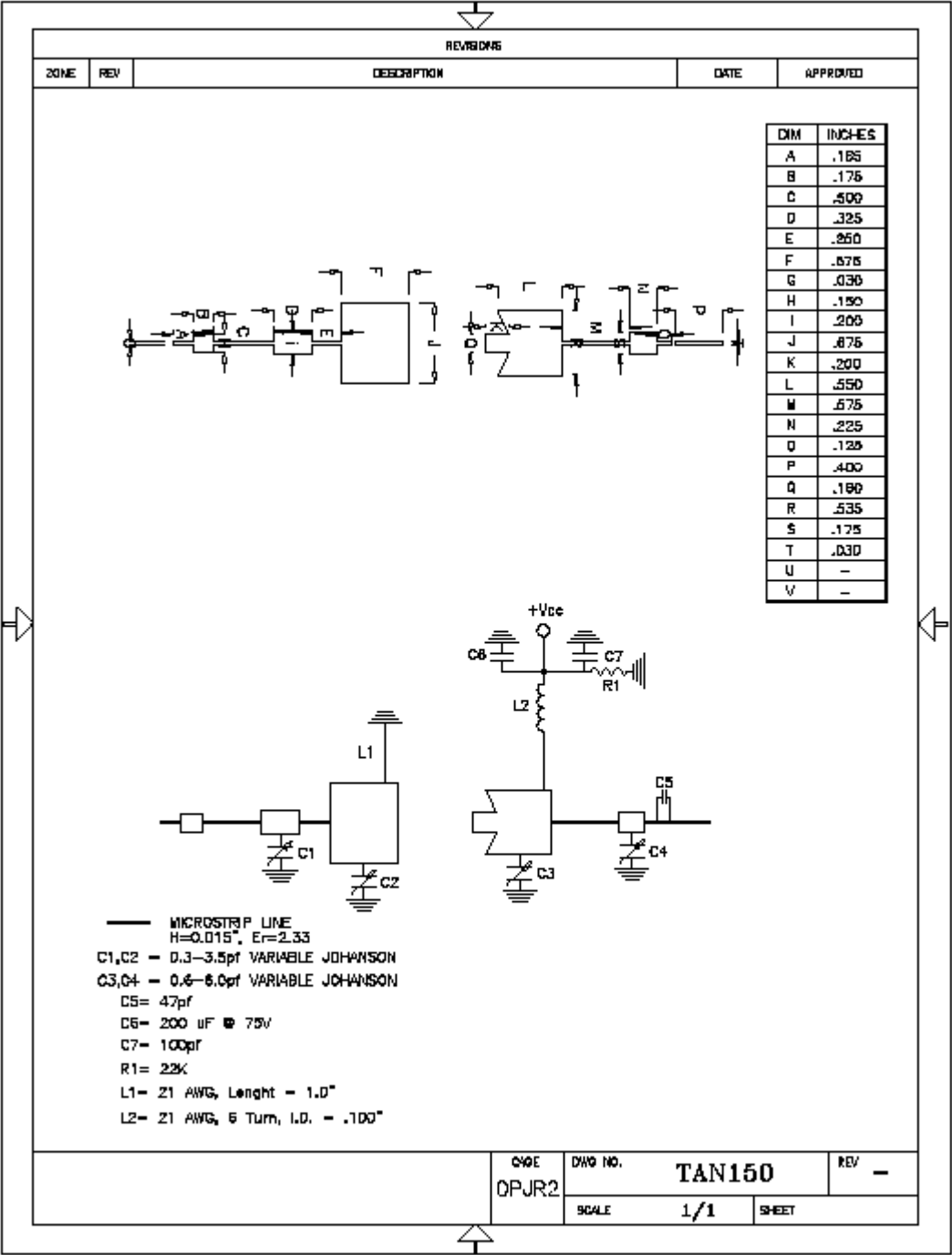
DWG NO.

55AT

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TAN150 TEST CIRCUIT:



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